

# 2SB1604, 2SB1604A

Silicon PNP epitaxial planar type

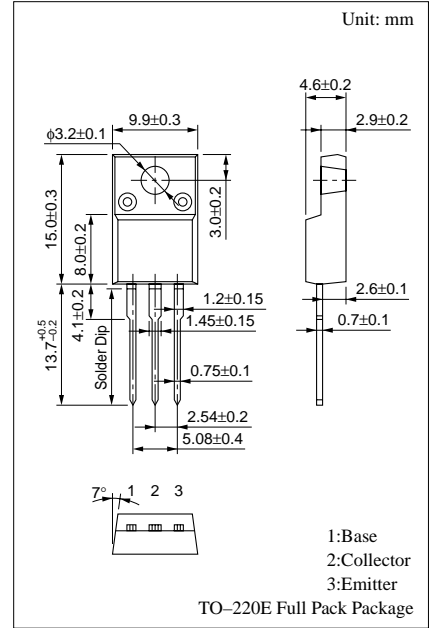
For low-voltage switching

## Features

- Low collector to emitter saturation voltage  $V_{CE(sat)}$
- High-speed switching
- Full-pack package with outstanding insulation, which can be installed to the heat sink with one screw

## Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ )

Parameter	Symbol	Ratings	Unit	
Collector to base voltage	2SB1604	-40	V	
	2SB1604A	-50		
Collector to emitter voltage	2SB1604	-20	V	
	2SB1604A	-40		
Emitter to base voltage	$V_{EBO}$	-5	V	
Peak collector current	$I_{CP}$	-20	A	
Collector current	$I_C$	-10	A	
Collector power dissipation	$P_C$	$T_C=25^\circ\text{C}$	40	W
		$T_a=25^\circ\text{C}$	2	
Junction temperature	$T_j$	150	$^\circ\text{C}$	
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$	



## Electrical Characteristics ( $T_C=25^\circ\text{C}$ )

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = -40\text{V}, I_E = 0$			-50	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -5\text{V}, I_C = 0$			-50	$\mu\text{A}$
Collector to emitter voltage	$V_{CEO}$	$I_C = -10\text{mA}, I_B = 0$	-20			V
			-40			
Forward current transfer ratio	$h_{FE1}$	$V_{CE} = -2\text{V}, I_C = -0.1\text{A}$	45			
	$h_{FE2}^*$	$V_{CE} = -2\text{V}, I_C = -3\text{A}$	90		260	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\text{A}, I_B = -0.33\text{A}$			-0.6	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10\text{A}, I_B = -0.33\text{A}$			-1.5	V
Transition frequency	$f_T$	$V_{CE} = -10\text{V}, I_C = -0.5\text{A}, f = 10\text{MHz}$		100		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		400		pF
Turn-on time	$t_{on}$	$I_C = -3\text{A}, I_{B1} = -0.1\text{A}, I_{B2} = 0.1\text{A}$		0.1		$\mu\text{s}$
Storage time	$t_{stg}$			0.5		$\mu\text{s}$
Fall time	$t_f$			0.1		$\mu\text{s}$

\* $h_{FE2}$  Rank classification

Rank	Q	P
$h_{FE2}$	90 to 180	130 to 260

